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SEMIANNUAL STATUS REPORT

National Aeronautics and Space Administration
Grant NGR 22-009-337

covering the period
November 16, 1968 - February 15, 1969

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March 20, 1969

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FACILITY FORM 302

N69-26419

(ACCESSION NUMBER)	(THRU)
4	
(PAGES)	(CODE)
CR 10438	09
(NASA CR OR TRR OR AD NUMBER)	(CATEGORY)

SUMMARY OF RESEARCH

During the period 16 November 1968 through 14 February 1969, advances have been made on both experimental and theoretical understanding of avalanche diodes.

Theoretical calculations of static negative resistance in avalanche diodes were done during the previous six months. During the past three months, emphasis has been more on the transient case. A computer program has been written and refined, to simulate the behavior of such a diode as a function of time. It is possible to excite the diode with an arbitrary current waveform and view not only the resulting voltage but also electron and hole profiles and electric-field profiles. A collection of the resulting profiles shows how the transient behaves, and studies have been made on a variety of diodes and currents. It is also possible to consider the diode as excited through a circuit, and work has begun on writing the appropriate programs to simulate this.

We expect that these programs can be used to justify a lumped-circuit model for the diode. This model can then be used to design practical circuits such as oscillators.

An example of the use of these programs is shown in Fig. 1. Each line represents a profile of electron-current density at a specific time (the time in psec and the corresponding voltage are printed at the left). Each symbol represents a range of electron-current values; thus, higher numbers represent higher values of electron current, and letters still higher values. The diode is a p-i-n diode with base width $10\ \mu$, excited with a constant current of $2 \times 10^6\ \text{A/m}^2$.

A series of runs for various driving currents (all constant) shows that the amount of voltage breakback produced by the transient depends upon the current. For stronger currents the breakback is much higher, and for currents not much larger than the current for Fig. 1, the breakback is so large that the computation cannot be trusted, and a more elaborate program will be necessary.

Experimentally, an IMPATT avalanche-diode oscillator has shown noise and power improvement at the fundamental as the higher (second

1340.5

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JN0= 1.000E 00, JPO= 1.000E -00, EO= 2.000E 07, 40 STEPS.  
DENGRD= .000E 00, DX= .250 MICRONS, DT= 2.50 PS.
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INDEX: - JM LESS THAN 1000 AMPS/SQUARE METER. OTHER SYMBOLS:
SYMBOL: 0 1 2 3 4 5 6 7 8 9 A B C D E F G H I J K L M N O P Q R
PWR OF 10: 3 3 3 3 3 4 4 4 4 4 5 5 5 5 5 6 6 6 6 6 7 7 7 7 7 8 8 8

TIME (PS)	VOLTAGE	
00	200.000	-----
25	204.868	-----
50	209.736	-----
75	214.605	-----
100	219.473	-----
125	224.341	-----
150	229.209	-----
175	234.077	-----
200	238.946	-----
225	243.814	-----
250	248.682	-----
275	253.550	-----
300	258.418	-----
325	263.287	-----
350	268.155	-----
375	273.022	-----
400	277.890	-----
425	282.756	110000-----
450	287.620	33322221111000-----
475	292.475	6655554444333222111000-----
500	297.293	99988877776665554443332211100-----
525	301.936	DCCCCBBBAAA99988877766555443322110-----
550	305.582	HGGGFFFEEDDDCCBBBAA99988776655433210---
575	303.463	KKJJJJJIIIIHHHGGGFFFEEDDDCCBBAA9887765431-
600	282.048	LLLLKKKKKKKKJJJJJJIIIIHHHGGGFFFEEDDCBBAA9875-
625	239.331	LLKKKKKKKKKKKKJJJJJJJJIIIIHHHGGGFFFEEDCB9-
650	188.700	KKKKKKKKJJJJJJJJJJJJJJIIIIIIHHHHGGGFFFEEDCB-
675	148.376	JJJJJJJJJJJJJIIIIIIHHHHHGGGFFFEEDDCBBAA986-
700	130.129	JJIIIIIIIKHHHHGGGFFFEEDDCBBAA9876543210---
725	128.820	HHHHGGGFFFEEDDCBBAA9876543210-----
750	133.512	EDDCBBAA9876543210-----
775	138.561	6543210-----
800	143.466	-----
825	148.337	-----
850	153.205	-----
875	158.074	-----
900	162.942	-----
925	167.810	-----
950	172.679	-----
975	177.547	-----
1000	182.415	-----

Fig. 1. Computer simulation of avalanche transients.

and third) harmonics were tuned. The variation in noise performance appears to be the important result, and a quantitative measure has shown that the tuning produced a 6-8 dB noise figure change when the oscillator was used as the local oscillator for a balanced mixer.

Incremental measurements of the avalanche impedance of the diode junction have been made as a function of the avalanche current in the range of frequencies from 4 GHz to 12 GHz. The negative real part still exists at 4 GHz, but is of little consequence, since the bulk series resistance of the diode overwhelms it. Considering both the real and imaginary parts of the impedance, there appears to be an optimum frequency at which to use the device as an oscillator. From these measurements, a small-signal model has been formed leading to a large-signal model of frequency-independent elements which we hope will predict the observed behavior regarding harmonic terminations.